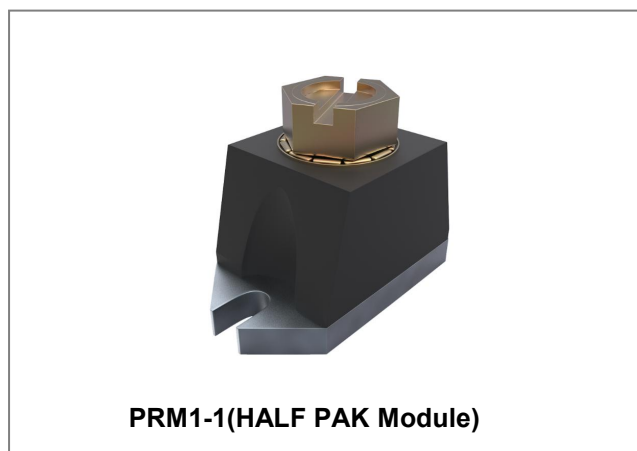


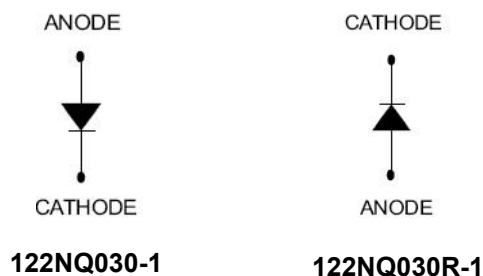
122NQ030/R-1 SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

The top side is terminal, the bottom side is base plate.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	30	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C = 110°C, rectangular wave form	120	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	2880	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 120A, Pulse, $T_J = 25\text{ }^{\circ}\text{C}$ @ 240A, Pulse, $T_J = 25\text{ }^{\circ}\text{C}$	0.47 -	0.49 0.59	V
	V_{F2}	@ 120A, Pulse, $T_J = 125\text{ }^{\circ}\text{C}$ @ 240A, Pulse, $T_J = 125\text{ }^{\circ}\text{C}$	0.38 -	0.41 0.54	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$, $T_J = 25\text{ }^{\circ}\text{C}$	0.3	10	mA
	I_{R2}	@ $V_R = \text{rated } V_R$, $T_J = 125\text{ }^{\circ}\text{C}$	300	560	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^{\circ}\text{C}$ $f_{\text{SIG}} = 1\text{MHz}$	5800	7400	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

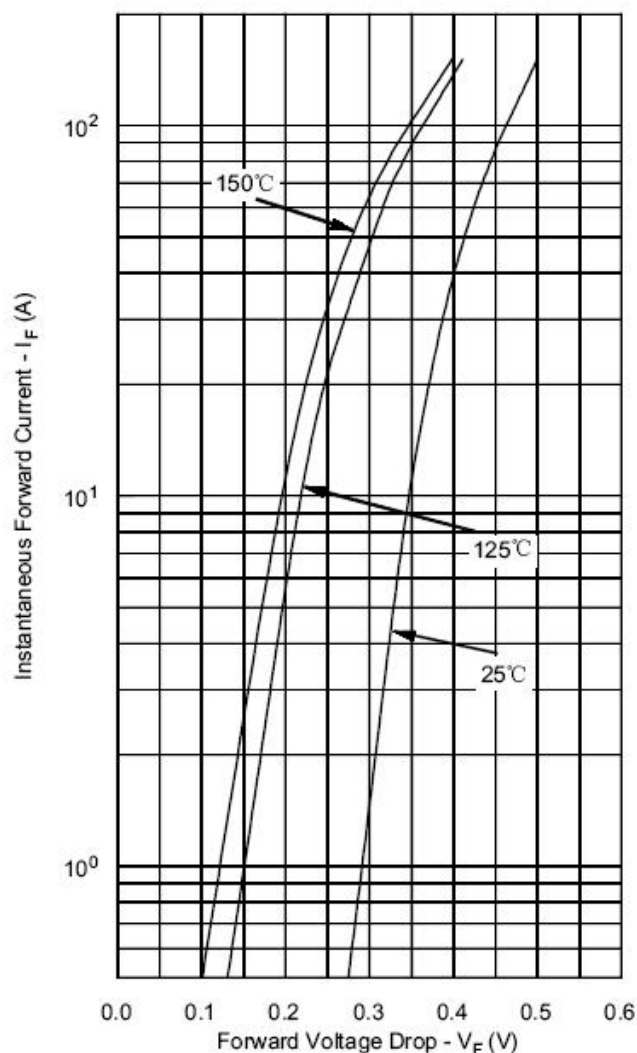
* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

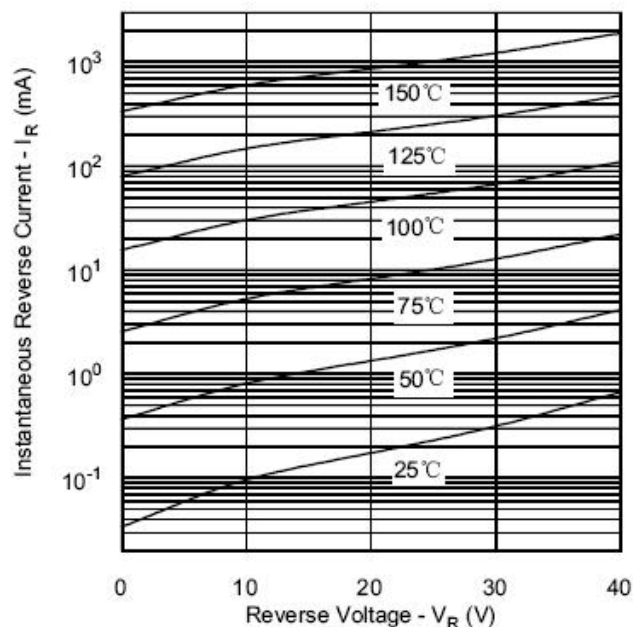
Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	T _J	-	-55 to +150		°C
Storage Temperature	T _{stg}	-	-55 to +150		°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	0.40		°C/W
Typical Thermal Resistance, case to Heat Sink	R _{θcs}	Mounting surface, smooth and greased	0.15		°C/W
Mounting Torque	T _M	Non-lubricated threads	Mounting Torque	23(min) 29(max)	Kg-cm
			Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	25.6		g
Case Style	PRM1-1				

Ratings and Characteristics Curves

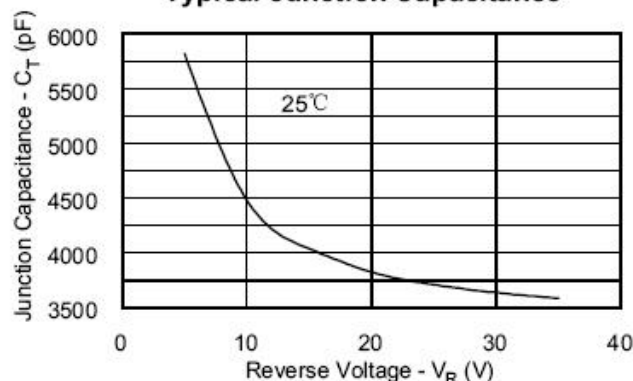
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



Ordering Information

Device	Package	Shipping
122NQ030(R)-1	PRM1-1(Pb-Free)	27pcs/ box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

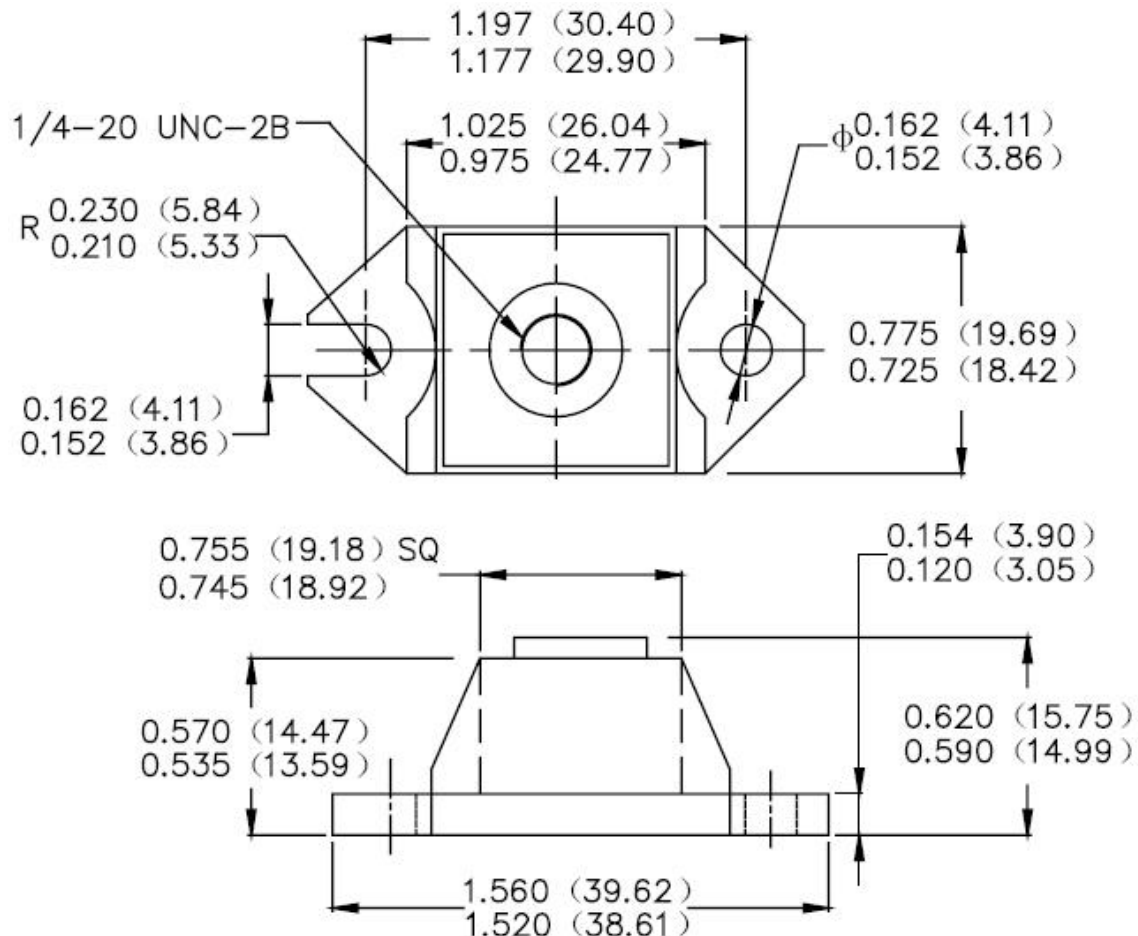


Where XXXX is YYWW

1st row SS YYWW
2nd row 122NQ030-1
SS = SS
YY = Year
WW = Week

Cautions: Molding resin
Epoxy resin UL:94V-0

Mechanical Dimensions PRM1-1 (Inches/Millimeters)



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